Complementary Silicon Power Plastic Transistors

These devices are designed for low power audio amplifier and low-current, high-speed switching applications.

Features

- High Collector-Emitter Sustaining Voltage
- High DC Current Gain
- Low Collector-Emitter Saturation Voltage
- High Current Gain Bandwidth Product
- Annular Construction for Low Leakages
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	100	Vdc
Collector-Base Voltage	V _{CB}	100	Vdc
Emitter-Base Voltage	V _{EB}	7.0	Vdc
Collector Current – Continuous	Ι _C	4.0	Adc
Collector Current – Peak	I _{CM}	8.0	Adc
Base Current	Ι _Β	10	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	PD	15 120	W mW/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

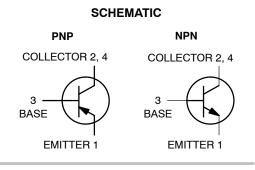
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	8.34	°C/W
Thermal Resistance, Junction-to-Ambient	θ_{JA}	83.4	°C/W



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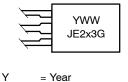
http://onsemi.com

4.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 100 VOLTS, 15 WATTS





MARKING DIAGRAM



WW = Work Week JE2x3 = Device Code x = 4 or 5

G = Pb-Free Package

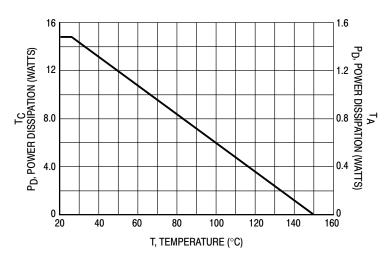
ORDERING INFORMATION

Device	Package	Shipping
MJE243G	TO-225 (Pb-Free)	500 Units/Box
MJE253G	TO-225 (Pb-Free)	500 Units/Box

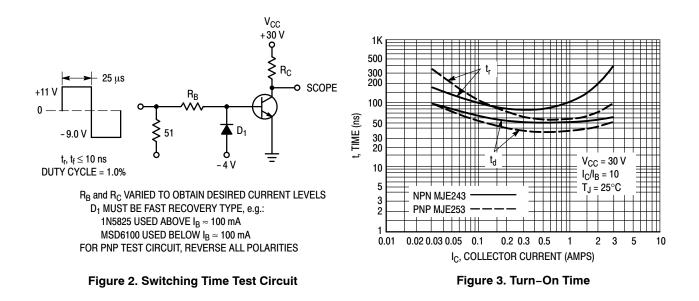
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS		•	•	•
Collector–Emitter Sustaining Voltage $(I_{C} = 10 \text{ mAdc}, I_{B} = 0)$	V _{CEO(sus)}	100	_	V
Collector Cutoff Current (V _{CB} = 100 Vdc, I _E = 0) (V _{CE} = 100 Vdc, I _E = 0, T _C = 125 $^{\circ}$ C)	I _{CBO}		0.1 0.1	μA mA
Emitter Cutoff Current (V_{BE} = 7.0 Vdc, I_C = 0)	I _{EBO}	-	0.1	μAdc
ON CHARACTERISTICS		•		
DC Current Gain ($I_C = 200 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 1.0 \text{ Adc}, V_{CE} = 1.0 \text{ Vdc}$)	h _{FE}	40 15	180 -	-
Collector-Emitter Saturation Voltage ($I_C = 500 \text{ mAdc}$, $I_B = 50 \text{ mAdc}$) ($I_C = 1.0 \text{ Adc}$, $I_B = 100 \text{ mAdc}$)	V _{CE(sat)}		0.3 0.6	V
Base–Emitter Saturation Voltage $(I_C = 2.0 \text{ Adc}, I_B = 200 \text{ mAdc})$	V _{BE(sat)}	-	1.8	V
Base-Emitter On Voltage (I _C = 500 mAdc, V _{CE} = 1.0 Vdc)	V _{BE(on)}	-	1.5	V
DYNAMIC CHARACTERISTICS	·			
Current–Gain – Bandwidth Product (I _C = 100 mAdc, V _{CE} = 10 Vdc, f _{test} = 10 MHz)	fT	40	_	MHz
Output Capacitance (V _{CB} = 10 Vdc, I _E = 0, f = 0.1 MHz)	C _{ob}	-	50	pF







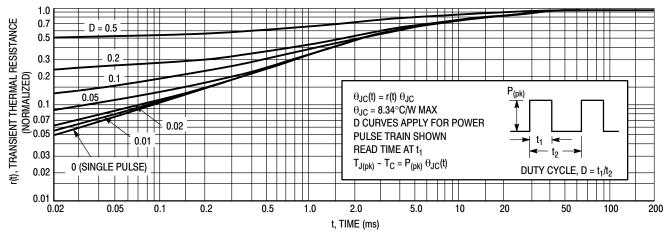


Figure 4. Thermal Response

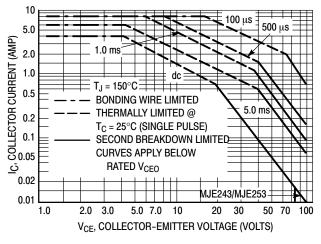
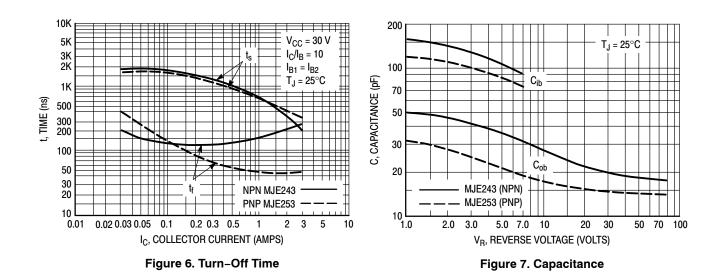
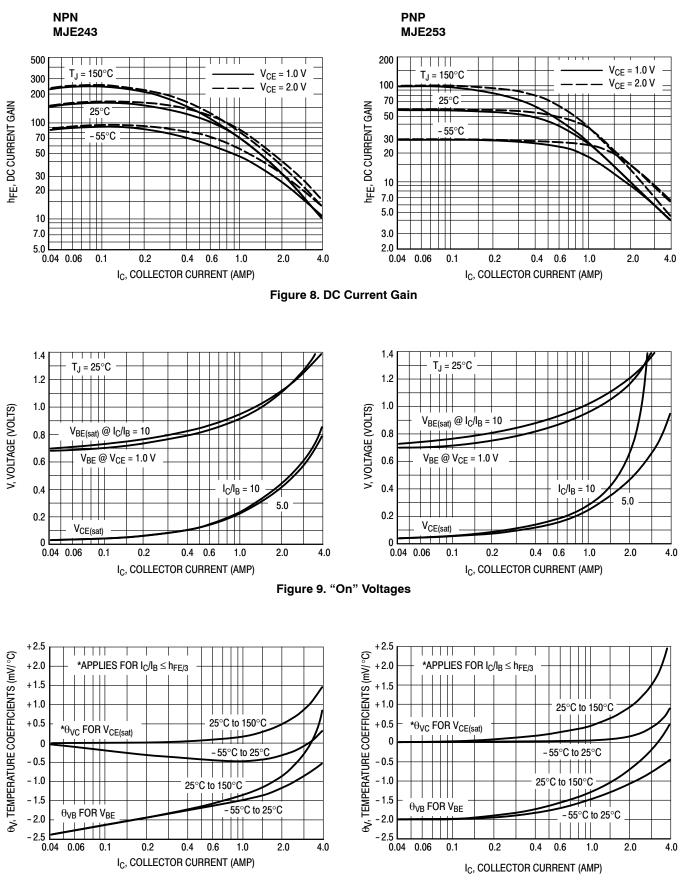


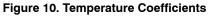
Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}$ C; T_{C} is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}$ C. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

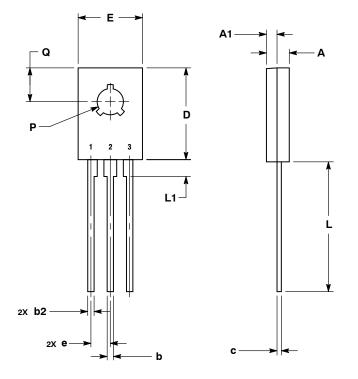






PACKAGE DIMENSIONS

TO-225 CASE 77-09 **ISSUE AA**



NOTES:

1. DIMENSIONING AND TOLERANCING PER

ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. NUMBER AND SHAPE OF LUGS OPTIONAL.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.40	3.00	
A1	1.00	1.50	
b	0.60	0.90	
b2	0.51	0.88	
C	0.39	0.63	
D	10.60	11.10	
Е	7.40	7.80	
е	2.04	2.54	
L	14.50	16.63	
L1	1.27	2.54	
Р	2.90	3.30	
Q	3.80	4.20	

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